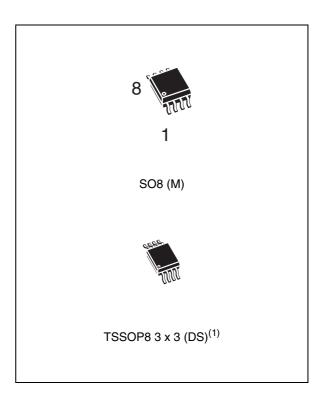


STM690A, STM692A, STM703 STM704, STM802, STM805, STM817/8/9

5 V supervisor with battery switchover

Features

- 5 V operating voltage
- NVRAM supervisor for external LPSRAM
- Chip-enable gating (STM818 only) for external LPSRAM (7 ns max prop delay)
- RST and RST outputs
- 200 ms (typ) t_{rec}
- Watchdog timer 1.6 sec (typ)
- Automatic battery switchover
- Low battery supply current 0.4 µA (typ)
- Power-fail comparator (PFI/PFO)
- Low supply current 40 µA (typ)
- Guaranteed RST (RST) assertion down to V_{CC} = 1.0 V
- Operating temperature: -40 °C to +85 °C (industrial grade)
- RoHS compliance
 - Lead-free components are compliant with the RoHS directive



1. Contact local ST sales office for availability.

Table 1. Device summary

Part number	Watchdog input	Active-low RST ⁽¹⁾	Active- high RST	Manual reset input ⁽¹⁾	Battery switch- over	Power-fail comparator	Chip- enable gating	Battery freshness seal
STM690A	1	✓			1	✓		
STM692A	1	✓			1	✓		
STM703		✓		✓	1	✓		
STM704		✓		✓	1	✓		
STM802L/M	1	✓			1	√		
STM805L	1		✓		1	✓		
STM817L/M	✓	✓			1	✓		✓
STM818L/M	1	✓			1		✓	✓
STM819L/M		✓		1	1	✓		1

^{1.} All RST and RST outputs are push-pull.

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C	TMAGO	A /60'	2 A /7 N	3/70//	802/805	/217/21	12/210
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Description 1

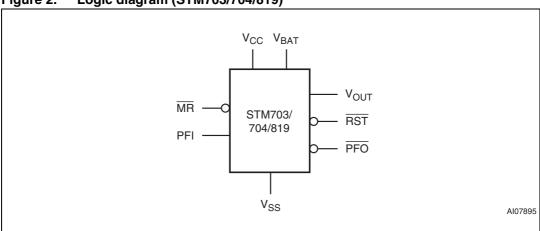
The STM690A/692A/703/704/802/805/817/818/819 supervisors are self-contained devices which provide microprocessor supervisory functions with the ability to non-volatize and write-protect external LPSRAM. A precision voltage reference and comparator monitors the V_{CC} input for an out-of-tolerance condition. When an invalid V_{CC} condition occurs, the reset output (RST) is forced low (or high in the case of RST). These devices also offer a watchdog timer (except for STM703/704/819) as well as a power-fail comparator (except for STM818) to provide the system with an early warning of impending power failure.

These devices are available in a standard 8-pin SOIC package or a space-saving 8-pin TSSOP package.

 V_{CC} V_{BAT} Vout WDI STM690A/ RST(RST)(1) 692A/802/ PFI 805/817 PFO V_{SS}

Logic diagram (STM690A/692/802/805/817) Figure 1.

1. For STM805, reset output is active-high.



Logic diagram (STM703/704/819) Figure 2.

Figure 3. Logic diagram (STM818)

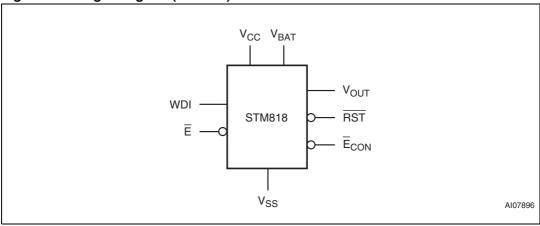
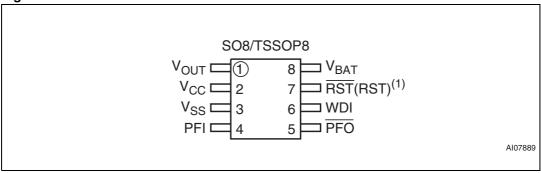


Table 2. Signal names

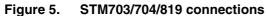
Push-button reset input
Watchdog input
Active-low reset output
Active-high reset outpu
Chip-enable input
Conditioned chip-enable output
Supply voltage output
Supply voltage
Backup supply voltage
Power-fail input
Power-fail output
Ground

^{1.} STM818

Figure 4. STM690A/692A/802/805/817 connections



1. For STM805, reset output is active-high.



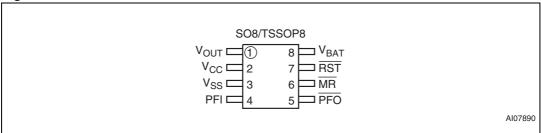
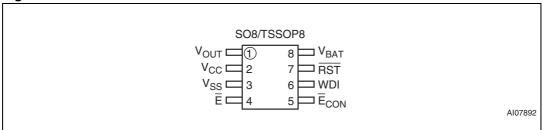


Figure 6. STM818 connections



1.1 Pin descriptions

1.1.1 MR

A logic low on $\overline{\text{MR}}$ asserts the reset output. Reset remains asserted as long as $\overline{\text{MR}}$ is low and for t_{rec} after $\overline{\text{MR}}$ returns high. This active-low input has an internal pull-up. It can be driven from a TTL or CMOS logic line, or shorted to ground with a switch. Leave open if unused.

1.1.2 WDI

If WDI remains high or low for 1.6 sec, the internal watchdog timer runs out and reset is triggered. The internal watchdog timer clears while reset is asserted or when WDI sees a rising or falling edge.

The watchdog function can be disabled by allowing the WDI pin to float.

1.1.3 **RST**

Pulses low for t_{rec} when triggered, and stays low whenever V_{CC} is below the reset threshold or when \overline{MR} is a logic low. It remains low for $\underline{t_{rec}}$ after either V_{CC} rises above the reset threshold, the watchdog triggers a reset, or \overline{MR} goes from low to high.

1.1.4 RST

Pulses high for t_{rec} when triggered, and stays high whenever V_{CC} is above the reset threshold or when \overline{MR} is a logic high. It remains high for t_{rec} after either V_{CC} falls below the reset threshold, the watchdog triggers a reset, or \overline{MR} goes from high to low.

1.1.5 V_{OUT}

When V_{CC} is above the switchover voltage (V_{SO}), V_{OUT} is connected to V_{CC} through a P-channel MOSFET switch. When V_{CC} falls below V_{SO} , V_{BAT} connects to V_{OUT} .

1.1.6 V_{BAT}

When V_{CC} falls below V_{SO} , V_{OUT} switches from V_{CC} to V_{BAT} . When V_{CC} rises above V_{SO} + hysteresis, Vout reconnects to V_{CC} . V_{BAT} may exceed V_{CC} . Connect to V_{CC} if no battery is used.

1.1.7 $\overline{\mathsf{E}}$

The input to the chip-enable gating circuit. Connect to ground if unused.

1.1.8 $\overline{\mathsf{E}}_{\mathsf{CON}}$

 \overline{E}_{CON} goes low only when \overline{E} is low and reset is not asserted. If \overline{E}_{CON} is low when reset is asserted, \overline{E}_{CON} will remain low for 15 μ s or until \overline{E} goes high, whichever occurs first. In the disabled mode, \overline{E}_{CON} is pulled up to V_{OUT} .

1.1.9 PFI

When PFI is less than V_{PFI} or when V_{CC} falls below 2.4 V (or V_{SO}), \overline{PFO} goes low; otherwise, \overline{PFO} remains high. Connect to ground if unused.

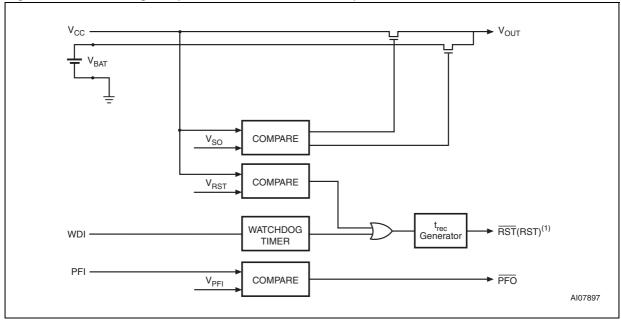
1.1.10 PFO

When PFI is less than V_{PFI} , or V_{CC} falls below 2.4 V (or V_{SO}), \overline{PFO} goes low; otherwise, \overline{PFO} remains high. Leave open if unused. Output type is push-pull.

Table 3. Pin description

	Р	in				
STM818	STM690A STM692A STM802 STM817	STM703 STM704 STM819	STM805	Name	Function	
-	-	6	-	MR	Push-button reset input	
6	6	-	6	WDI	Watchdog input	
7	7	7	-	RST	Active-low reset output	
-	-	-	7	RST	Active-high reset output	
1	1	1	1	V _{OUT}	Supply output for external LPSRAM	
2	2	2	2	V _{CC}	Supply voltage	
8	8	8	8	V _{BAT}	Backup battery input	
4	-	-	-	Ē	Chip-enable input	
5	-	-	-	E _{CON}	Conditioned chip-enable output	
-	4	4	4	PFI	Power-fail input	
-	5	5	5	PFO	Power-fail output (push-pull)	
3	3	3	3	V _{SS}	Ground	

Figure 7. Block diagram (STM690A/692A/802/805/817)



1. For STM805, reset output is active-high.

Figure 8. Block diagram (STM703/704/819)

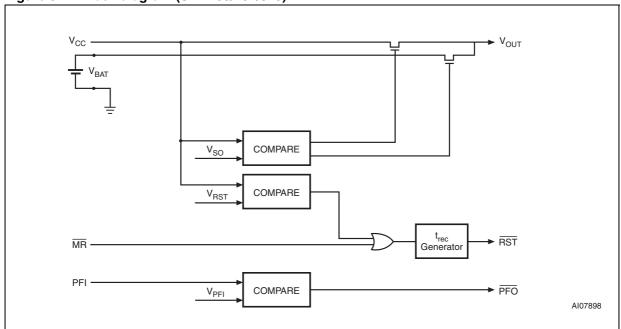


Figure 9. Block diagram (STM818)

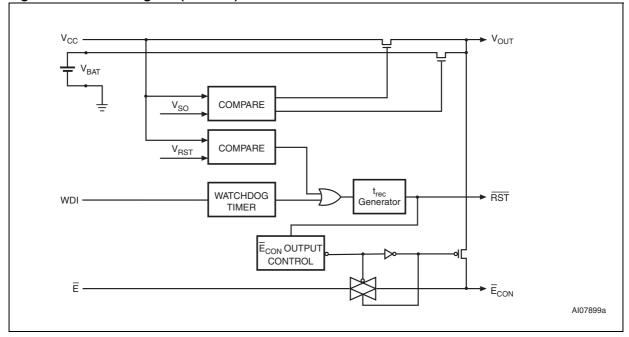
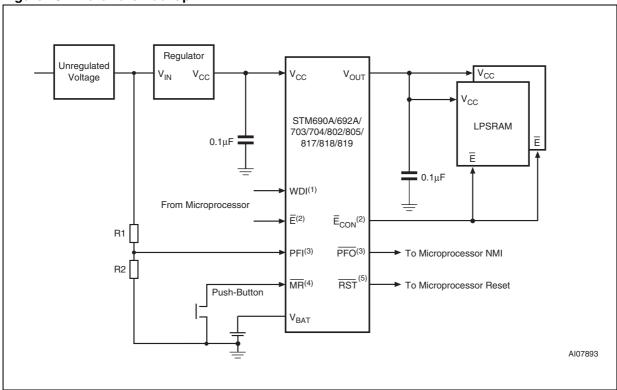


Figure 10. Hardware hookup



- 1. For STM690A/692A/802/805/817/818.
- 2. For STM818 only.
- 3. Not available on STM818.
- 4. For STM703/704/819.
- 5. Active high on STM805.

2 Operation

2.1 Reset output

The STM690A/692A/703/704/802/805/817/818/819 Supervisor asserts a reset signal to the MCU whenever V_{CC} goes below the reset threshold (V_{RST}), a watchdog time-out occurs, or when the Push-button Reset Input (\overline{MR}) is taken low. \overline{RST} is guaranteed to be a logic low (logic high for STM805) for 0V < V_{CC} < V_{RST} if VBAT is greater than 1 V. Without a backup battery, \overline{RST} is guaranteed valid down to V_{CC} =1 V.

During power-up, once V_{CC} exceeds the reset threshold an internal timer keeps \overline{RST} low for the reset time-out period, t_{rec} . After this interval \overline{RST} returns high.

If V_{CC} drops below the reset threshold, \overline{RST} goes low. Each time \overline{RST} is asserted, it stays low for at least the reset time-out period (t_{rec}). Any time V_{CC} goes below the reset threshold the internal timer clears. The reset timer starts when V_{CC} returns above the reset threshold.

2.2 Push-button reset input (STM703/704/819)

A logic low on \overline{MR} asserts reset. Reset remains asserted while \overline{MR} is low, and for t_{rec} (see *Figure 41*) after it returns high. The \overline{MR} input has an internal 40 k Ω pull-up resistor, allowing it to be left open if not used. This input can be driven with TTL/CMOS-logic levels or with open-drain/collector outputs. Connect a normally open momentary switch from \overline{MR} to GND to create a manual reset function; external debounce circuitry is not required. If \overline{MR} is driven from long cables or the device is used in a noisy environment, connect a 0.1 μ F capacitor from \overline{MR} to GND to provide additional noise immunity. \overline{MR} may float, or be tied to V_{CC} when not used.

2.3 Watchdog input (NOT available on STM703/704/819)

The watchdog timer can be used to detect an out-of-control MCU. If the MCU does not toggle the Watchdog Input (WDI) within t_{WD} (1.6 sec typ), the reset is asserted. The internal watchdog timer is cleared by either:

- 1. a reset pulse, or
- 2. by toggling WDI (high-to-low or low-to-high), which can detect pulses as short as 50ns. If WDI is tied high or low, a reset pulse is triggered every 1.8 sec ($t_{WD} + t_{rec}$).

The timer remains cleared and does not count for as long as reset is asserted. As soon as reset is released, the timer starts counting (see *Figure 42*).

Note: 1

- 1 The watchdog function may be disabled by floating WDI or tri-stating the driver connected to WDI. When tri-stated or disconnected, the maximum allowable leakage current is 10 μA and the maximum allowable load capacitance is 200 pF.
- 2 Input pulses less than 20 ns will be ignored.

2.4 Backup battery switchover

In the event of a power failure, it may be necessary to preserve the contents of external SRAM through V_{OUT} . With a backup battery installed with voltage V_{BAT} , the devices automatically switch the SRAM to the backup supply when V_{CC} falls.

Note:

When the battery is first connected without V_{CC} power applied, the device does not immediately provide backup battery voltage on V_{OUT} . Only after V_{CC} exceeds V_{RST} will the switchover operate as described below. This mode allows a battery to be attached during manufacturing but not used until after the system has been activated for the first time. As a result, no battery power is consumed by the device during storage and shipment. For the STM81x devices, the battery freshness seal can be initiated again by following the procedure outlined in Section 2.12. If the backup battery is not used, connect both V_{BAT} and V_{OUT} to V_{CC} .

Whenever V_{CC} falls below the switchover voltage, V_{SO} , V_{OUT} is connected to V_{BAT} through a 100 Ω switch. V_{SO} is the lesser of V_{BAT} and V_{RST} . Choosing the lesser allows the device to be powered by V_{CC} for as long as possible before switching over thereby maximizing the battery life.

Assuming $V_{BAT} > 2.0$ V, switchover at V_{SO} ensures that battery backup mode is entered before V_{OUT} gets too close to the 2.0 V minimum required to reliably retain data in most external SRAMs. When V_{CC} recovers, hysteresis is used to avoid oscillation around the V_{SO} point. V_{OUT} is connected to V_{CC} through a 3 Ω PMOS power switch.

Note:

The backup battery may be removed while V_{CC} is valid, assuming V_{BAT} is adequately decoupled (0.1 μ F typ), without danger of triggering a reset.

Table 4. I/O status in battery backup

V _{OUT}	Connected to V _{BAT} through internal switch
V _{CC}	Disconnected from V _{OUT}
PFI	Disabled
PFO	Logic low
Ē	High impedance
Ē _{CON}	Logic high
WDI	Watchdog timer is disabled
MR	Disabled
RST	Logic low
RST	Logic high
V_{BAT}	Connected to V _{OUT}

2.5 Chip-enable gating (STM818 only)

Internal gating of the chip-enable (\overline{E}) signal prevents erroneous data from corrupting the external CMOS RAM in the event of an undervoltage condition. The STM818 uses a series transmission gate from \overline{E} to \overline{E}_{CON} (see *Figure 11*). During normal operation (reset not asserted), the \overline{E} transmission gate is enabled and passes all \overline{E} transitions. When reset is asserted, this path becomes disabled, preventing erroneous data from corrupting the CMOS RAM. The short propagation delay from \overline{E} to \overline{E}_{CON} enables the STM818 to be used with most μ Ps. If \overline{E} is low when reset asserts, \overline{E}_{CON} remains low for typically 15 μ s (or until \overline{E} goes high) to permit the current WRITE cycle to complete. Connect \overline{E} to V_{SS} if unused.

2.6 Chip-enable input (STM818 only)

The chip-enable transmission gate is disabled and \overline{E} is high impedance (disabled mode) while reset is asserted. During a power-down sequence when V_{CC} passes the reset threshold, the chip-enable transmission gate disables and \overline{E} immediately becomes high impedance if the voltage at \overline{E} is high. If \overline{E} is low when reset asserts, the chip-enable transmission gate will disable 15 μ s after reset asserts (see *Figure 12*). This permits the current WRITE cycle to complete during power-down.

Any time a reset is generated, the chip-enable transmission gate remains disabled and \overline{E} remains high impedance (regardless of \overline{E} activity) for the reset time-out period. When the chip-enable transmission gate is enabled, the impedance of \overline{E} appears as a 40 Ω resistor in series with the load at \overline{E}_{CON} . The propagation delay through the chip-enable transmission gate depends on V_{CC} , the source impedance of the drive connected to \overline{E} , and the loading on \overline{E}_{CON} . The chip-enable propagation delay is production tested from the 50% point on \overline{E} to the 50% point on \overline{E}_{CON} using a 50 Ω driver and a 50 pF load capacitance (see *Figure 39*). For minimum propagation delay, minimize the capacitive load at \overline{E}_{CON} and use a low-output impedance driver.

2.7 Chip-enable output (STM818 only)

When the chip-enable transmission gate is enabled, the impedance of \overline{E}_{CON} is equivalent to a 40 Ω resistor in series with the source driving \overline{E} . In the disabled mode, the transmission gate is off and an active pull-up connects \overline{E}_{CON} to V_{OUT} (see *Figure 11*). This pull-up turns off when the transmission gate is enabled.



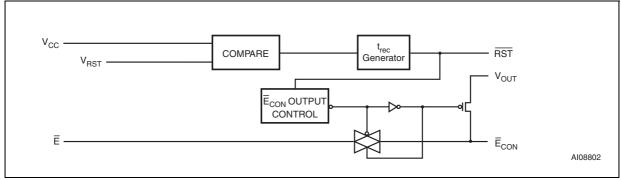
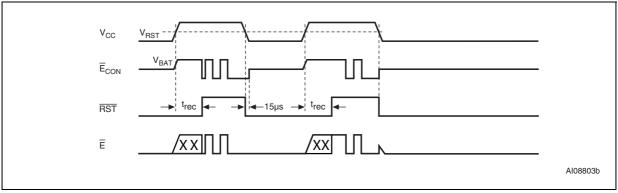


Figure 12. Chip-enable waveform



2.8 Power-fail input/output (NOT available on STM818)

The Power-fail Input (PFI) is compared to an internal reference voltage (independent from the V_{RST} comparator). If PFI is less than the power-fail threshold (V_{PFI}), the Power-Fail Output (\overline{PFO}) will go low. This function is intended for use as an undervoltage detector to signal a failing power supply. Typically PFI is connected through an external voltage divider (see *Figure 12*) to either the unregulated DC input (if it is available) or the regulated output of the V_{CC} regulator. The voltage divider can be set up such that the voltage at PFI falls below V_{PFI} several milliseconds before the regulated V_{CC} input to the STM690A/692A/703/704/802/805/817/818/819 Supervisor or before the microprocessor drops below the minimum operating voltage. This provides several milliseconds of advanced warning that power is about to fail.

During battery backup, the power-fail comparator turns off and \overline{PFO} goes (or remains) low (see *Figure 13* below and *Figure 14*). This occurs after V_{CC} drops below 2.4 V (or V_{SO}). When power returns, \overline{PFO} is forced high (STM817/819 only), irrespective of V_{PFI} for the WRITE protect time (t_{rec}). At the end of this time, the power-fail comparator is enabled and \overline{PFO} follows PFI. If the comparator is unused, PFI should be connected to V_{SS} and \overline{PFO} left unconnected. \overline{PFO} may be connected to \overline{MR} on the STM703/704/818 so that a low voltage on PFI will generate a reset output.

2.9 Applications information

These supervisor circuits are not short-circuit protected. Shorting V_{OUT} to ground - excluding power-up transients such as charging a decoupling capacitor - destroys the device. Decouple both V_{CC} and V_{BAT} pins to ground by placing 0.1 μF capacitors as close to the device as possible.

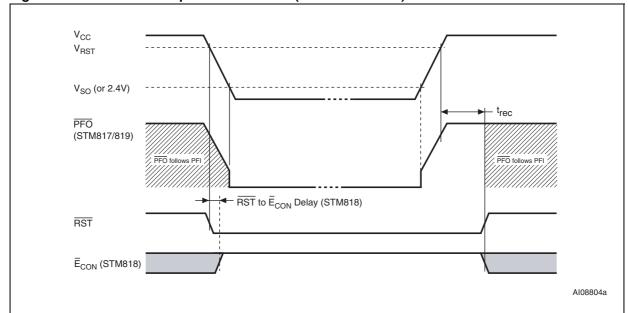
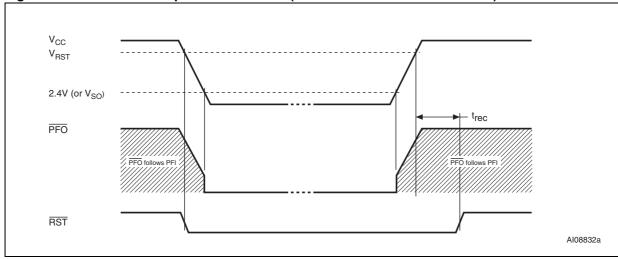


Figure 13. Power-fail comparator waveform (STM817/818/819)





2.10 Using a SuperCap™ as a backup power source

SuperCapsTM are capacitors with extremely high capacitance values (e.g., 0.47 F) for their size. *Figure 15* shows how to use a SuperCap as a backup power source. The SuperCap may be connected through a diode to the 5 V supply. Since V_{BAT} can exceed V_{CC} while V_{CC} is above the reset threshold, there are no special precautions for using these supervisors with a SuperCap.

2.11 Negative-going V_{CC} transients

The STM690A/692A/703/704/802/805/817/818/819 Supervisors are relatively immune to negative-going V_{CC} transients (glitches). Figure 37 shows typical transient duration versus reset comparator overdrive (for which the STM690A/692A/703/704/802/805/817/818/819 will NOT generate a reset pulse). The graph was generated using a negative pulse applied to V_{CC} , starting at V_{RST} + 0.3 V and ending below the reset threshold by the magnitude indicated (comparator overdrive). The graph indicates the maximum pulse width a negative V_{CC} transient can have without causing a reset pulse. As the magnitude of the transient increases (further below the threshold), the maximum allowable pulse width decreases. Any combination of duration and overdrive which lies under the curve will NOT generate a reset signal. Typically, a V_{CC} transient that goes 100 mV below the reset threshold and lasts 40 μ s or less will not cause a reset pulse. A 0.1 μ F bypass capacitor mounted as close as possible to the V_{CC} pin provides additional transient immunity.

2.12 Battery freshness seal (STM817/818/819)

The battery freshness seal disconnects the backup battery from internal circuitry and V_{OUT} until it is needed. This allows an OEM to ensure that the backup battery connected to V_{BAT} will be fresh when the final product is put to use. To enable the freshness seal:

- 1. Connect a battery to V_{BAT}
- 2. Ground PFO
- 3. Bring V_{CC} above the reset threshold and hold it there until reset is deasserted following the reset timeout period and
- 4. Bring V_{CC} down again (*Figure 16*)

Use the same procedure for the STM818, but ground \overline{E}_{CON} instead of \overline{PFO} . Once the battery freshness seal is enabled (disconnecting the backup battery from internal circuitry and anything connected to V_{OUT}), it remains enabled until V_{CC} is brought above V_{RST} .

Figure 15. Using a SuperCap™

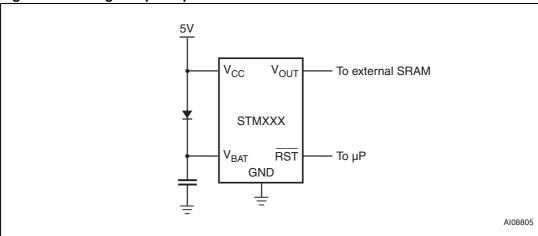
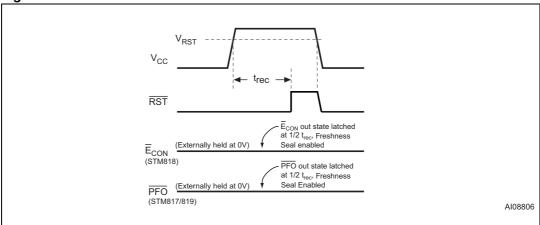


Figure 16. Freshness seal enable waveform



3 Typical operating characteristics

Note: Typical values are at $T_A = 25$ °C.

Figure 17. V_{CC} to V_{OUT} on-resistance vs. temperature

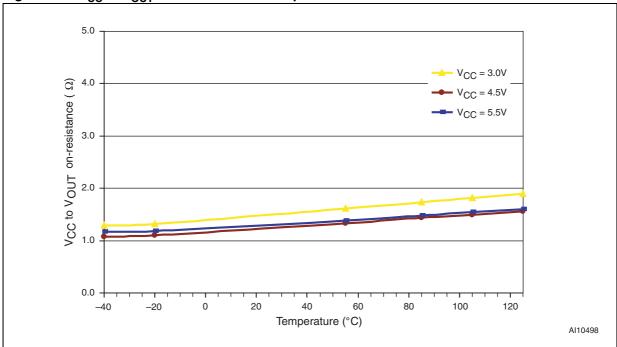


Figure 18. V_{BAT} to V_{OUT} on-resistance vs. temperature

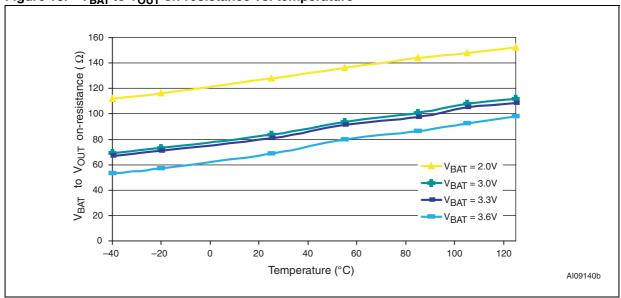


Figure 19. Supply current vs. temperature (no load)

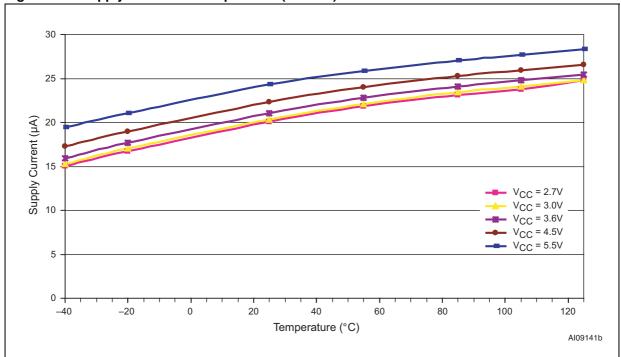


Figure 20. Battery current vs. temperature

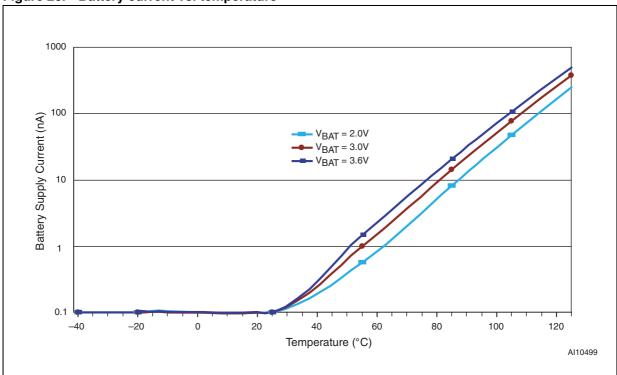


Figure 21. V_{PFI} threshold vs. temperature

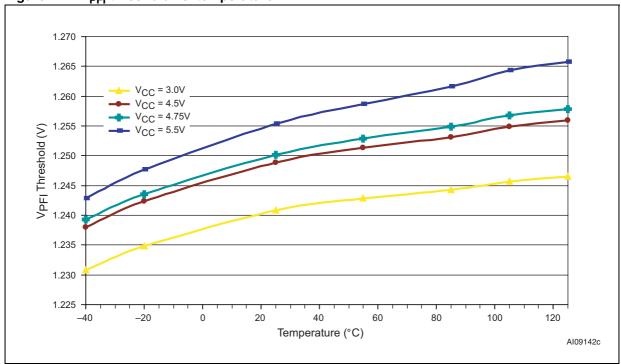
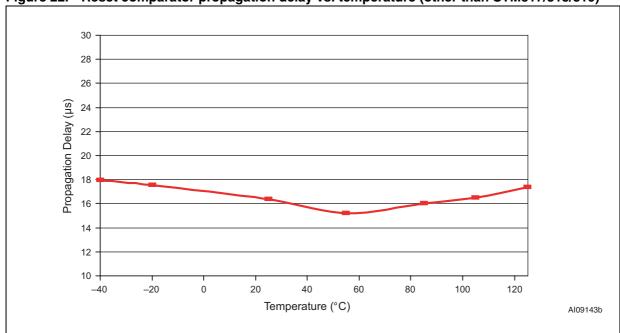


Figure 22. Reset comparator propagation delay vs. temperature (other than STM817/818/819)



350 **1**v/ms 300 - 10V/ms Propagation Delay (µs) 250 200 150 100 50 0 -20 0 20 40 60 80 100 120 -40 Temperature (°C) AI11100

Figure 23. Reset comparator propagation delay vs. temperature (V_{BAT} = 3.0 V; STM817/818/819)



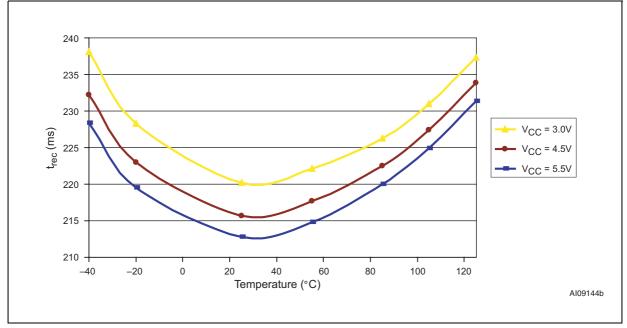


Figure 25. Normalized reset threshold vs. temperature

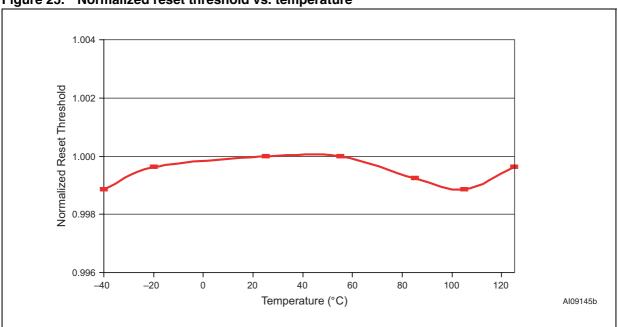


Figure 26. Watchdog time-out period vs. temperature

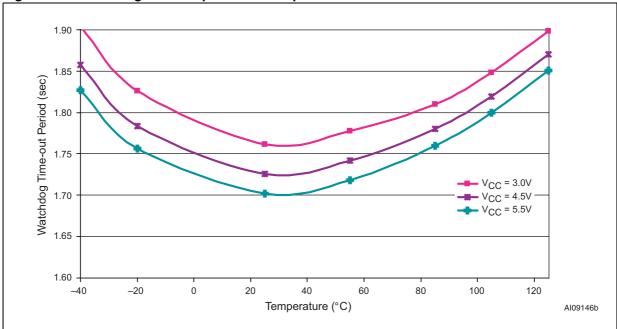


Figure 27. $\overline{\mathsf{E}}$ to $\overline{\mathsf{E}}_{\mathsf{CON}}$ on-resistance vs. temperature

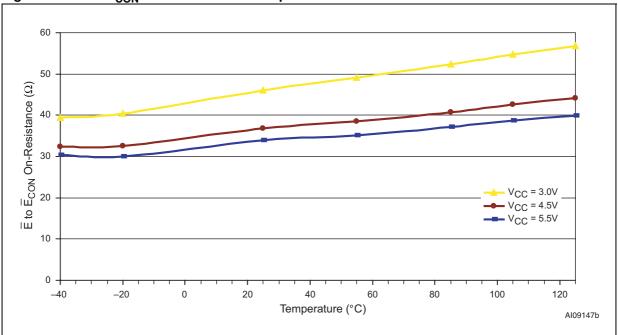


Figure 28. PFI to PFO propagation delay vs. temperature

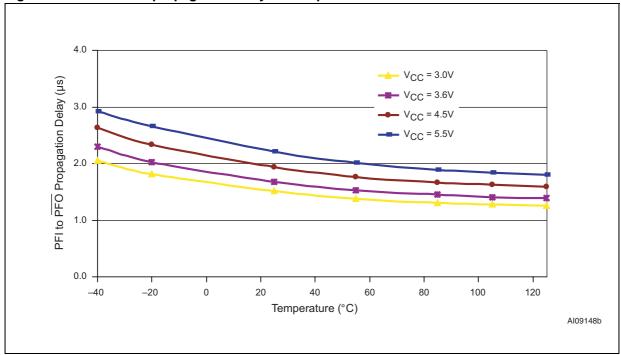


Figure 29. Output voltage vs. load current (V_{CC} = 5 V; V_{BAT} = 2.8 V; T_A = 25 °C)

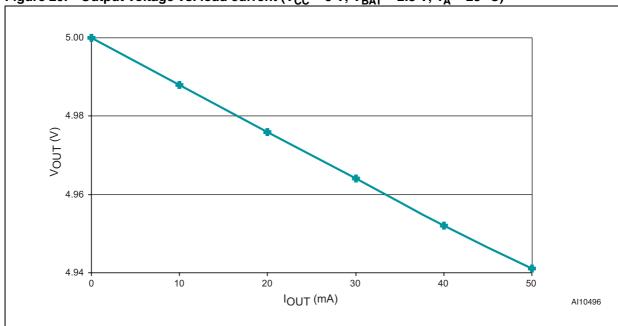


Figure 30. Output voltage vs. load current ($V_{CC} = 0 \text{ V}$; $V_{BAT} = 2.8 \text{ V}$; $T_A = 25 ^{\circ}\text{C}$)

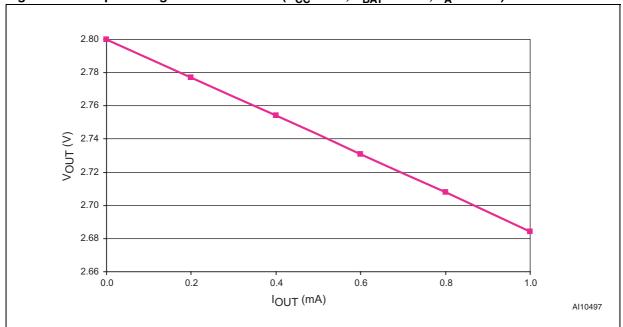


Figure 31. RST output voltage vs. supply voltage

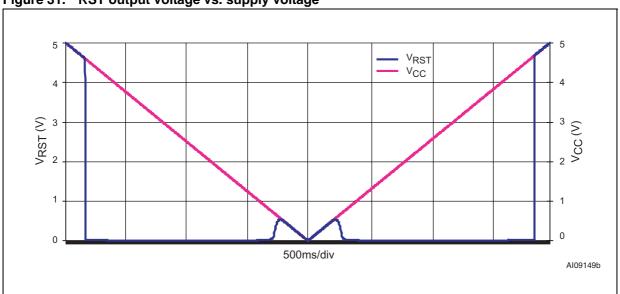


Figure 32. RST output voltage vs. supply voltage

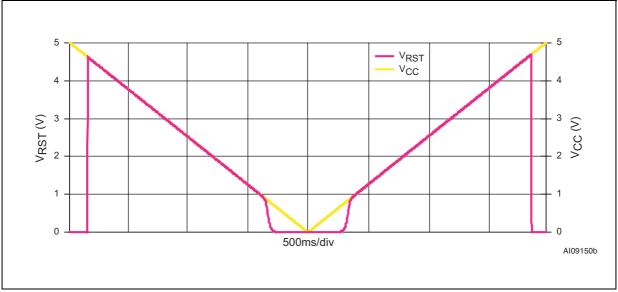


Figure 33. RST response time (assertion)

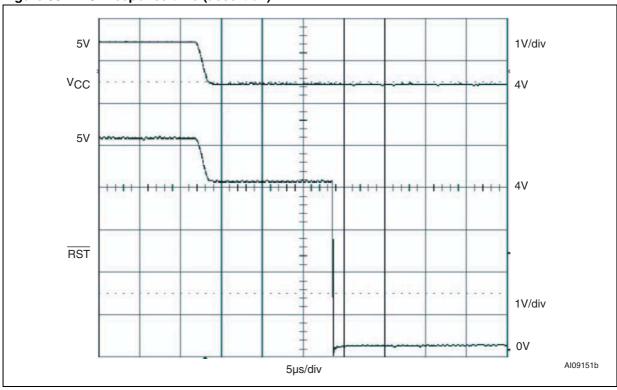
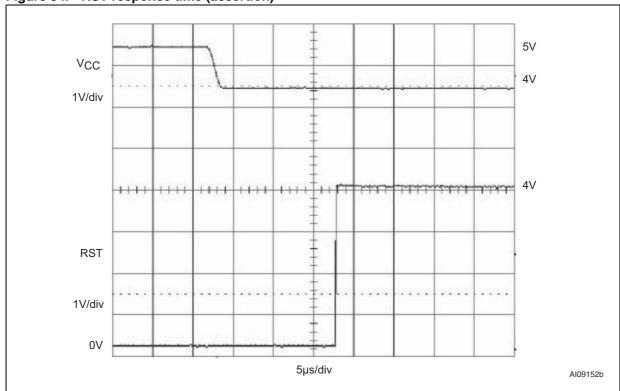


Figure 34. RST response time (assertion)



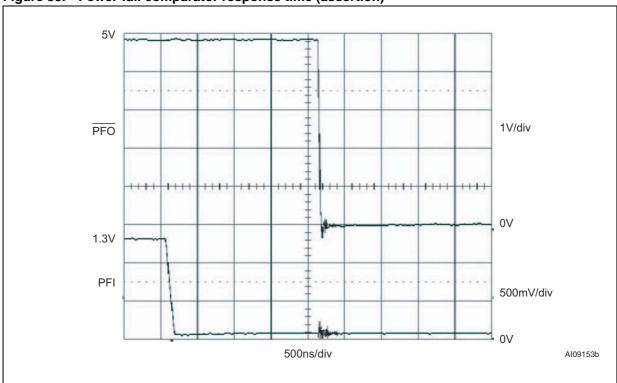


Figure 35. Power-fail comparator response time (assertion)



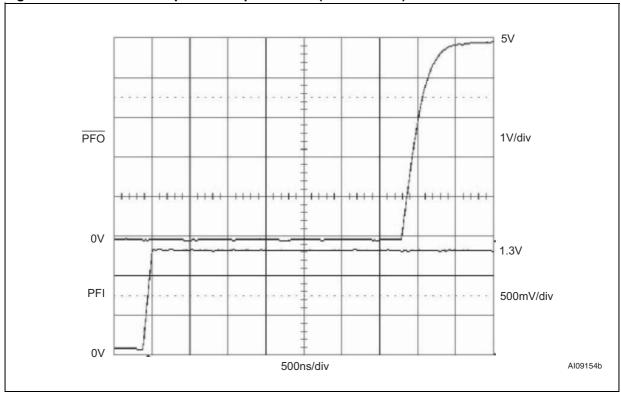


Figure 37. Maximum transient duration vs. reset threshold overdrive

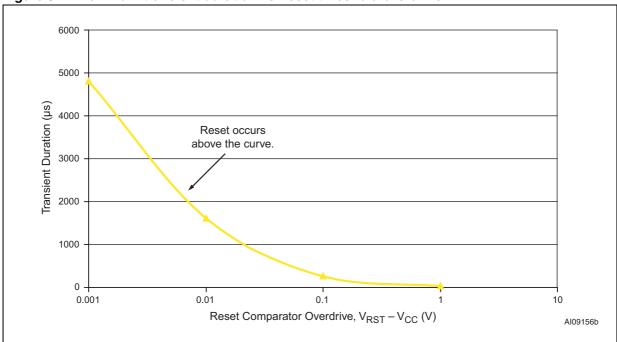
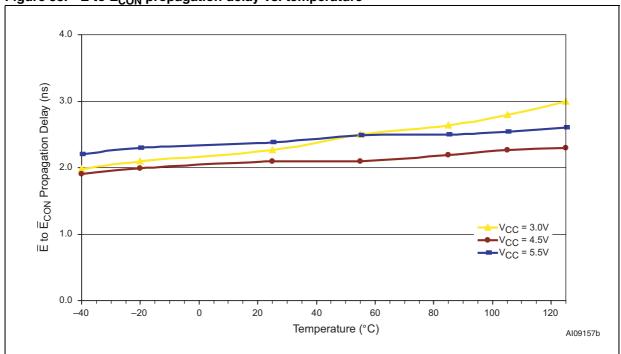


Figure 38. \overline{E} to \overline{E}_{CON} propagation delay vs. temperature



4 Maximum ratings

Stressing the device above the rating listed in the absolute maximum ratings table may cause permanent damage to the device. These are stress ratings only and operation of the device at these or any other conditions above those indicated in the operating sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Table 5. Absolute maximum ratings

Symbol	Parameter	Value	Unit
T _{STG}	Storage temperature (V _{CC} off)	-55 to 150	°C
T _{SLD} ⁽¹⁾	Lead solder temperature for 10 seconds	260	°C
V _{IO}	Input or output voltage	-0.3 to V_{CC} +0.3	V
V _{CC} /V _{BAT}	Supply voltage	-0.3 to 6.0	V
Io	Output current	20	mA
P _D	Power dissipation	320	mW

^{1.} Reflow at peak temperature of 260 °C. The time above 255 °C must not exceed 30 seconds.

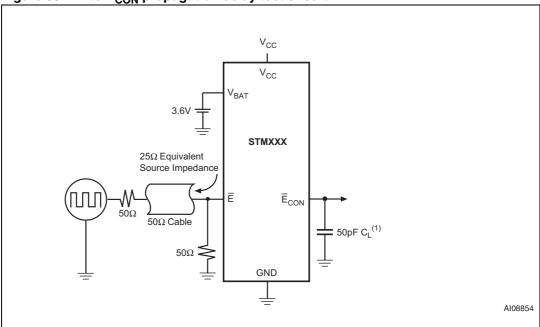
5 DC and AC parameters

This section summarizes the operating measurement conditions, and the DC and AC characteristics of the device. The parameters in the DC and AC characteristics Tables that follow, are derived from tests performed under the measurement conditions summarized in *Table 6: Operating and AC measurement conditions*. Designers should check that the operating conditions in their circuit match the operating conditions when relying on the quoted parameters.

Table 6. Operating and AC measurement conditions

Parameter	STM690A/692A/703/704/802/805/ 817/818/819	Unit
V _{CC} /V _{BAT} supply voltage	1.0 to 5.5	V
Ambient operating temperature (T _A)	-40 to 85	°C
Input rise and fall times	≤5	ns
Input pulse voltages	0.2 to 0.8V _{CC}	V
Input and output timing ref. voltages	0.3 to 0.7V _{CC}	V

Figure 39. \overline{E} to \overline{E}_{CON} propagation delay test circuit



1. C_L includes load capacitance and scope probe capacitance.

Figure 40. AC testing input/output waveforms

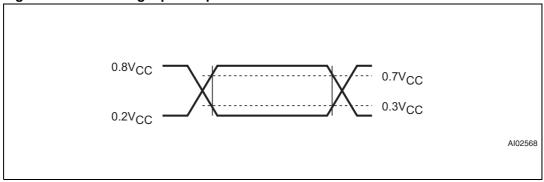
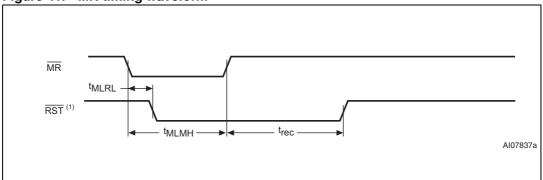


Figure 41. MR timing waveform



1. RST for STM805.

Figure 42. Watchdog timing

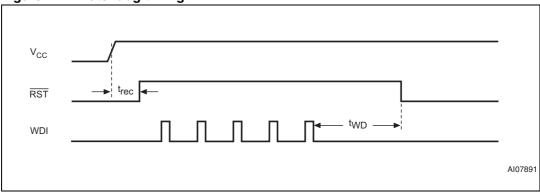


Table 7. DC and AC characteristics

Sym	Alter- native	Description	Test condition ⁽¹⁾	Min	Тур	Max	Unit
V_{CC} , $V_{BAT}^{(2)}$		Operating voltage	T _A = -40 to +85 °C	1.2 ⁽³⁾		5.5	٧
		V _{CC} supply current	Excluding I _{OUT} (V _{CC} < 5.5 V)		25	60	μΑ
I _{CC}		V _{CC} supply current in battery backup mode	Excluding I_{OUT} ($V_{BAT} = 2.3 \text{ V}$, $V_{CC} = 2.0 \text{ V}$, $\overline{MR} = V_{CC}$)		25	35	μA
I _{BAT} ⁽⁴⁾		V _{BAT} supply current in battery backup mode	Excluding I _{OUT} (V _{BAT} = 3.6 V)		0.4	1.0	μA
			I _{OUT1} = 5 mA ⁽⁵⁾	V _{CC} – 0.03	V _{CC} – 0.015		٧
V _{OUT1}		V _{OUT} voltage (active)	I _{OUT1} = 75 mA	V _{CC} – 0.3	V _{CC} – 0.15		V
			$I_{OUT1} = 250 \mu A,$ $V_{CC} > 2.5 V^{(5)}$	V _{CC} – 0.0015	V _{CC} – 0.0006		٧
V _{OUT2}		V _{OUT} voltage (battery backup)	I _{OUT2} = 250 μA, V _{BAT} = 2.3 V	V _{BAT} – 0.1	V _{BAT} – 0.034		٧
0012		раскир)	$I_{OUT2} = 1 \text{ mA}, V_{BAT} = 2.3 \text{ V}$		V _{BAT} – 0.14		٧
		V _{CC} to V _{OUT} on-resistance			3	4	Ω
		V _{BAT} to V _{OUT} on-resistance			100		Ω
		Input leakage current (MR)	4.5 V < V _{CC} < 5.5 V	75	125	300	μA
I _{LI}		Input leakage current (PFI)	0 V < V _{IN} < V _{CC}	-25	2	+25	nA
		Input leakage current	WDI = V _{CC} , time average		120	160	μΑ
		(WDI) ⁽⁶⁾	WDI = GND, time average	-20	-15		μΑ
V _{IH}		Input high voltage (MR)	4.5 V < V _{CC} < 5.5 V	2.0			٧
V _{IH}		Input high voltage (WDI)	V _{RST} (max) < V _{CC} < 5.5 V	0.7V _{CC}			٧
V _{IL}		Input low voltage (MR)	4.5 V < V _{CC} < 5.5 V			0.8	٧
V _{IL}		Input low voltage (WDI)	V _{RST} (max) < V _{CC} < 5.5 V			0.3V _{CC}	٧
,,		Output low voltage (PFO, RST, RST)	$V_{CC} = V_{RST}$ (max), $I_{SINK} = 3.2$ mA			0.3	٧
V _{OL}		Output low voltage (E _{CON})	$V_{CC} = V_{RST}$ (max), $I_{OUT} = 1.6$ mA, $\overline{E} = 0$ V			0.2V _{CC}	٧
V		Output low voltage (RST)	$\begin{split} I_{SINK} &= 50 \; \mu\text{A}, \; V_{CC} = 1.0 \; \text{V}, \\ V_{BAT} &= V_{CC} \; , \; T_{A} = 0 ^{\circ}\text{C} \; \text{to} \; 85 ^{\circ}\text{C} \end{split}$		_	0.3	٧
V _{OL}		Output low voltage (nST)	I_{SINK} = 100 μ A, V_{CC} = 1.2 V, V_{BAT} = V_{CC}			0.3	٧

Table 7. DC and AC characteristics (continued)

Sym	Alter- native	Description	Test condition ⁽¹⁾		Min	Тур	Max	Unit
		Output high voltage (RST, RST)	$I_{SOURCE} = 1 \text{ mA}$ $V_{CC} = V_{RST} \text{ (max)}$		2.4			V
V _{OH}		Output high voltage (\overline{E}_{CON})	$V_{CC} = V_{RST}$ (max), $I_{OUT} = 1.6$ mA, $\overline{E} = V_{CC}$		0.8V _{CC}			V
		Output high voltage (PFO)	$I_{SOURCE} = 75 \mu A,$ $V_{CC} = V_{RST} (max)$		0.8V _{CC}			V
V _{OH}		Output high voltage	$\begin{split} I_{SOURCE} &= 4~\mu\text{A},~V_{CC} = 1.1~\text{V},\\ V_{BAT} &= V_{CC}~,~T_{A} = 0^{\circ}\text{C}~\text{to}~85^{\circ}\text{C} \end{split}$				0.8	V
				A, $V_{CC} = 1.2 \text{ V}$, = V_{CC}			0.9	V
,		V _{OH} battery backup (RST, RST)	I _{SOURCE} = 100 μA, V _{CC} = 0, V _{BAT} = 2.8 V		0.8V _{BAT}			V
V _{OHB}		V _{OH} battery backup (E _{CON})		= 75 μA, _{BAT} = 2.8 V	0.8V _{BAT}			V
Power-fa	ail comp	parator (NOT available on	STM818)					
V _{PFI}		PFI input threshold	PFI falling (V _{CC} = 5 V)	All other versions	1.20	1.25	1.30	V
				STM802	1.225	1.250	1.275	٧
t _{PFD}		PFI to PFO propagation delay				2		μs
I _{SC}		PFO output short to GND current	V _{CC} = 5 V, V _{PFO} = 0 V		0.1	0.75	2.0	mA
Battery	switcho	ver						
		Battery backup	Power-down	V _{RST} > V _{BAT}		V_{BAT}		٧
		switchover voltage ⁽⁷⁾⁽⁸⁾ (V _{CC} < V _{BAT} & V _{CC} < V _{RST})	rower-down	V _{RST} < V _{BAT}		V_{RST}		V
VSO			Power-up	V _{RST} > V _{BAT}		V_{BAT}		V
			i ower-up	$V_{RST} < V_{BAT}$		V_{RST}		V
		Hysteresis				40		mV
Reset th	reshold	ds						
V _{RST}		Dood throok ald (9)	STM690A/703, STM8XXL		4.50	4.65	4.75	V
		Reset threshold ⁽⁹⁾	STM692A/704, STM8XXM		4.25	4.40	4.50	V
		Reset threshold hysteresis				25		mV
		V _{CC} to RST delay (from V _{RST} , V _{CC} falling at 10 V/ms)	om STM817/818/819			100		μs

Table 7. DC and AC characteristics (continued)

Sym	Alter- native	Description Test condition ⁽¹⁾		Min	Тур	Max	Unit
t _{REC}		RST pulse width		140	200	280	ms
Push-b	utton res	set input (STM703/704/819)				
		MR pulse width	STM703/704	150			ns
t _{MLMH}	t _{MR}		STM819	1			μs
+		MR to RST output delay	STM703/704			250	ns
t _{MLMR}	t _{MRD}	Win to not output delay	STM819		120		ns
		MR glitch immunity	STM819		100		ns
		MR pull-up resistor	$\overline{MR} = 0 \text{ V}, \text{ V}_{CC} = 5 \text{ V}$	45	63	85	kΩ
Watchd	og time	r (NOT available on STM70	03/704/819)				
	t _{WD}	Watchdog timeout period	V _{RST} (max) < V _{CC} < 5.5 V	1.12	1.60	2.24	s
		WDI pulse width	V _{RST} (max) < V _{CC} < 5.5 V	50			ns
Chip-en	able ga	ting (STM818 only)					•
		\overline{E} to \overline{E}_{CON} resistance	V _{CC} = V _{RST} (max)		40	150	Ω
		E to E _{CON} propagation delay	4.5 V < V _{CC} < 5.5 V		2	7	ns
		Reset to \overline{E}_{CON} high delay	(Power-down)		15		μs
		E _{CON} short circuit current	$V_{CC} = 5 \text{ V, disable mode,}$ $\overline{E} = \text{logic high, } \overline{E}_{CON} = 0 \text{ V}$	0.1	0.75	2.0	mA

- 1. Valid for ambient operating temperature: $T_A = -40$ to 85 °C; $V_{CC} = 4.75$ V to 5.5 V for "L" versions; $V_{CC} = 4.5$ V to 5.5 V for "M" versions; and $V_{BAT} = 2.8$ V (except where noted).
- 2. V_{CC} supply current, logic input leakage, watchdog functionality, push-button reset functionality, PFI functionality, state of RST and RST tested at $V_{BAT} = 3.6 \text{ V}$, and $V_{CC} = 5.5 \text{ V}$. The state of RST or RST and PFO is tested at $V_{CC} = V_{CC}$ (min). Either V_{CC} or V_{BAT} can go to 0 V if the other is greater than 2.0 V.
- 3. V_{CC} (min) = 1.0 V for T_A = 0 °C to +85 °C.
- 4. Tested at V_{BAT} = 3.6 V, V_{CC} = 3.5 V and 0 V.
- 5. Guaranteed by design.
- 6. WDI input is designed to be driven by a three-state output device. To float WDI, the "high impedance mode" of the output device must have a maximum leakage current of 10 μA and a maximum output capacitance of 200 pF. The output device must also be able to source and sink at least 200 μA when active.
- 7. When $V_{BAT} > V_{CC} > V_{RST}$, V_{OUT} remains connected to V_{CC} until V_{CC} drops below V_{RST} .
- 8. When $V_{RST} > V_{CC} > V_{BAT}$, V_{OUT} remains connected to V_{CC} until V_{CC} drops below the battery voltage $(V_{BAT}) 75$ mV.
- 9. For V_{CC} falling.

6 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

A2 D ddd

A1 \(\alpha \)

SOA

Figure 43. SO8 - 8-lead plastic small outline, 150 mils body width, package mechanical drawing

Note: Drawing is not to scale.

Table 8. SO8 - 8-lead plastic small outline, 150 mils body width, package mechanical data

Symbol	mm			inches		
	Тур	Min	Max	Тур	Min	Max
Α	-	1.35	1.75	-	0.053	0.069
A1	-	0.10	0.25	-	0.004	0.010
В	-	0.33	0.51	-	0.013	0.020
С	-	0.19	0.25	-	0.007	0.010
D	-	4.80	5.00	-	0.189	0.197
ddd	-	-	0.10	-	-	0.004
Е	-	3.80	4.00	-	0.150	0.157
е	1.27	-	-	0.050	-	-
Н	-	5.80	6.20	-	0.228	0.244
h	-	0.25	0.50	-	0.010	0.020
L	-	0.40	0.90	-	0.016	0.035
α	-	0°	8°	-	0°	8°
N	8				8	

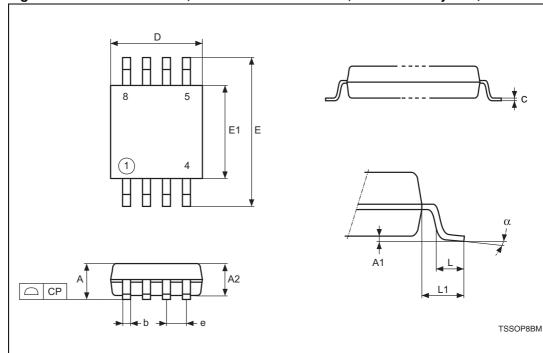


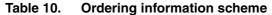
Figure 44. TSSOP8 - 8-lead, thin shrink small outline, 3 x 3 mm body size, outline

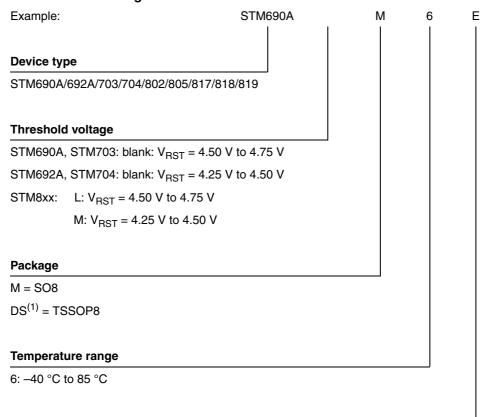
Note: Drawing is not to scale.

Table 9. TSSOP8 - 8-lead, thin shrink small outline, 3 x 3 mm body size, mechanical data

Symbol	mm			inches		
	Тур	Min	Max	Тур	Min	Max
Α	-	-	1.10	-	-	0.043
A1	-	0.05	0.15	-	0.002	0.006
A2	0.85	0.75	0.95	0.034	0.030	0.037
b	-	0.25	0.40	-	0.010	0.016
С	-	0.13	0.23	-	0.005	0.009
СР	-	-	0.10	-	-	0.004
D	3.00	2.90	3.10	0.118	0.114	0.122
е	0.65	-	-	0.026	-	-
Е	4.90	4.65	5.15	0.193	0.183	0.203
E1	3.00	2.90	3.10	0.118	0.114	0.122
L	0.55	0.40	0.70	0.022	0.016	0.030
L1	0.95	-	-	0.037	-	-
α	-	0°	6°	-	0°	6°
N	8				8	

7 Part numbering





Shipping method

E = ECOPACK® package, tubes

F = ECOPACK® package, tape & reel

1. Contact local ST sales office for availability.

For other options or for more information on any aspect of this device, please contact the ST sales office nearest you.

Table 11. Marking description

Part number	Reset threshold	Package	Topside marking
STM690A	4.65 V	SO8	690A
STM692A	4.40 V	SO8	692A
STM703	4.65 V	SO8	703
STM704	4.40 V	SO8	704
STM802L	4.65 V	SO8	802L
STM802M	4.40 V	SO8	802M
STM805L	4.65 V	SO8	805L
OTM0471	A CE V	SO8	0171
STM817L	4.65 V	TSSOP8	817L
CTM017M	4.40 V	SO8	017M
STM817M		TSSOP8	817M
STM818L	A CE V	SO8	818L
STWIGTOL	4.65 V	TSSOP8	010L
STM818M	4.40 V	SO8	818M
STIVIOTOIVI	4.40 V	TSSOP8	O I OIVI
STM819L	4.65 V	SO8	819L
2 I MIO 1AF	4.00 V	TSSOP8	019L
STM819M	A 40 V	SO8	819M
311/10131/1	4.40 V	TSSOP8	019101

8 Revision history

Table 12. Document revision history

Date	Revision	Changes	
Oct-2003	1	Initial release.	
31-Oct-2003	1.1	Update DC characteristics (<i>Table 7</i>).	
22-Dec-2003	2	Reformatted; updated characteristics (cover page, <i>Figure 2</i> , <i>3</i> , <i>6</i> , <i>7</i> , <i>8</i> , <i>9</i> , <i>10</i> , <i>11</i> , <i>12</i> , <i>13</i> , <i>14</i> , <i>16</i> , <i>Table 3</i> , <i>4</i> , <i>7</i> , <i>9</i> , <i>11</i>).	
16-Jan-2004	2.1	Add typical characteristics (<i>Figure 18, 19, 21, 22, 24, 25, 26, 27, 28, 31, 32, 33, 34, 35, 36, 37, 38</i>).	
08-Apr-2004	2.2	Update characteristics (<i>Figure 12, 22, 28, 32, 33, 34, 37</i> ; <i>Table 1, 7</i>).	
25-May-2004	3	Remove references to "open drain" (cover page, 4, 7; Table 2); update characteristics (Table 3, 7).	
05-Jul-2004	4	Update package availability, pin description; promote document (cover page, <i>Figure 13, 14</i> ; <i>Table 3, 7, 10</i>).	
29-Sep-2004	5	Clarify root part numbers, pin descriptions (Figure 10, 12, 39; Table 7, 10).	
01-Mar-2005	6	Update characteristics (<i>Figure 17, 18, 19, 20, 21, 22, 23, 24, 25, 26, 27, 28, 29, 30, 31, 32, 33, 34, 35, 36, 37, 38</i>)	
20-Jan-2006	7	Correct marking, update lead-free text (Table 10, 11)	
21-Oct-2008	8	Reformatted, minor text changes; updated <i>Table 3, 4, 7, 10, Figure 9, 10, 11, 12, 16, 39, Section 6: Package mechanical data.</i>	
20-Nov-2009	9	Updated text in Section 6, Table 5.	
18-Aug-2010	10	Updated Section 2.4: Backup battery switchover.	

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